

Chip Specification

General Description:

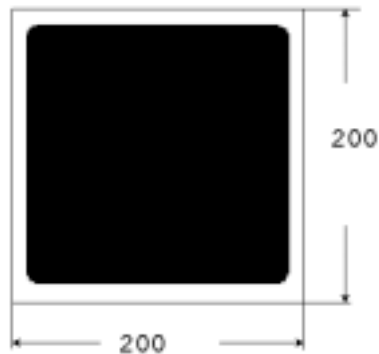
Schottky Diode chips with Mo-barrier for switch mode power rectifiers with the following features:

- * **Guard-ring for stress protection**
- * **Extremely low forward voltage**
- * **125 °C operation junction temperature**
- * **reverse avalanche behavior**

Mechanical Data:

MBR5045 passivated Silicon Chip

Dimension(mil):	200X200 mil
Thickness:	350 +- 20 μ m
Metallization:	
Top (Anode) :	AlAg
Bottom (Cathode) :	TiNiAg



Forward Current (A):	50A
Reverse Voltage (V):	>45V

Type	Chip	VF(V)@25 C	VF(V)@125 C	I _{RM} @V _{RMM}
	size(mil)	at I _f =50A	at I _f =50A	at 25 C
MBR5045	200X200	600mV	550mV	0,6mA

* expected value for recommended assembling with both side soldering
Typical device :1N6392

Note: Other voltages & Top Metal AL are available

